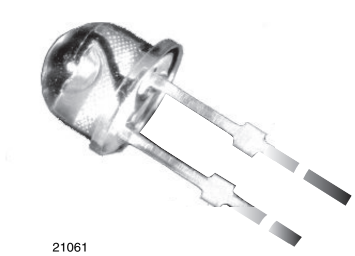
High Speed Infrared Emitting Diode, 830 nm, GaAlAs Double Hetero



FEATURES

- Package type: leaded
- Package form: T-1¾
- Dimensions (in mm): Ø 5
- Leads with stand-off
- Peak wavelength: λ_p = 830 nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: φ = ± 38°
- Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth: f_c = 24 MHz
- Good spectral matching to Si photodetectors
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

RoHS COMPLIANT
GREEN (5-2008)**

DESCRIPTION

TSHG5510 is an infrared, 830 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

APPLICATIONS

- Infrared radiation source for operation with CMOS cameras (illumination)
- High speed IR data transmission

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
TSHG5510	32	± 38	830	15

Note
- Test conditions see table “Basic Characteristics“

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSHG5510	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾

Note
- MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	t_p/T = 0.5, t_p = 100 µs	I_{FM}	200	mA
Surge forward current	t_p = 100 µs	I_{FSM}	1	A
Power dissipation		P_V	180	mW
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	- 40 to + 85	°C
Storage temperature range		T_{stg}	- 40 to + 100	°C
Soldering temperature	t ≤ 5 s, 2 mm from case	T_{sd}	260	°C
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	R_{thJA}	230	K/W

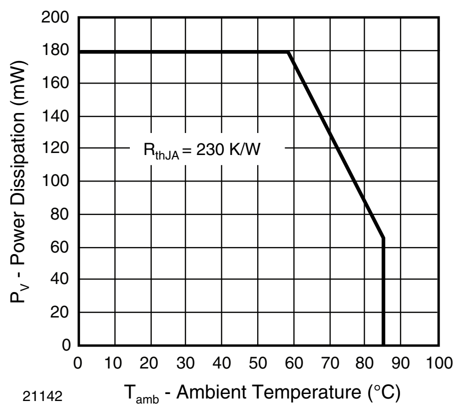


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

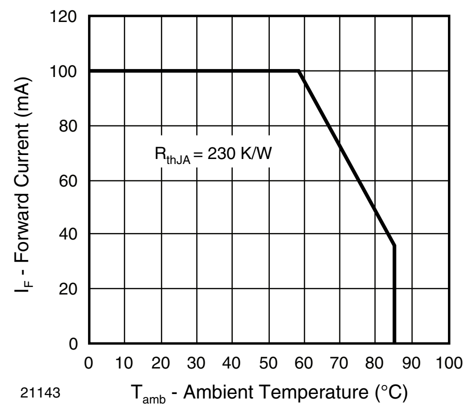


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I_F = 100 mA, t_p = 20 ms	V_F	1.3	1.45	1.7	V
	I_F = 450 mA, t_p = 100 µs	V_F	1.5	1.75	2.1	V
	I_F = 1 A, t_p = 100 µs	V_F		2.1		V
Temperature coefficient of V_F	I_F = 1 mA	TK_{VF}		- 1.8		mV/K
Reverse current	V_R = 5 V	I_R			10	µA
Junction capacitance	V_R = 0 V, f = 1 MHz, E = 0	C_j		110		pF
Radiant intensity	I_F = 100 mA, t_p = 20 ms	I_e	18	32	54	mW/sr
	I_F = 1 A, t_p = 100 µs	I_e		320		mW/sr
Radiant power	I_F = 100 mA, t_p = 20 ms	ϕ_e		55		mW
Temperature coefficient of ϕ_e	I_F = 100 mA	$TK\phi_e$		- 0.35		%/K
Angle of half intensity		φ		± 38		deg
Peak wavelength	I_F = 100 mA	λ_p		830		nm
Spectral bandwidth	I_F = 100 mA	$\Delta\lambda$		55		nm
Temperature coefficient of λ_p	I_F = 100 mA	$TK\lambda_p$		0.25		nm/K
Rise time	I_F = 100 mA	t_r		15		ns
Fall time	I_F = 100 mA	t_f		15		ns
Cut-off frequency	I_{DC} = 70 mA, I_{AC} = 30 mA pp	f_c		24		MHz

BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

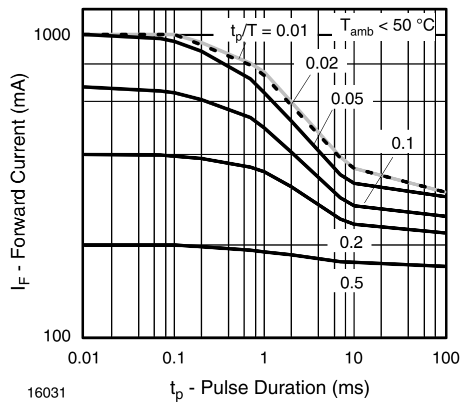


Fig. 3 - Pulse Forward Current vs. Pulse Duration

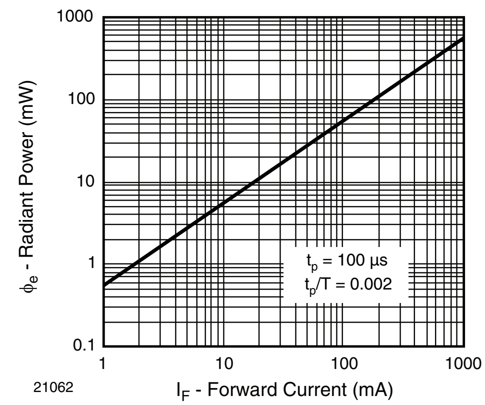


Fig. 6 - Radiant Power vs. Forward Current

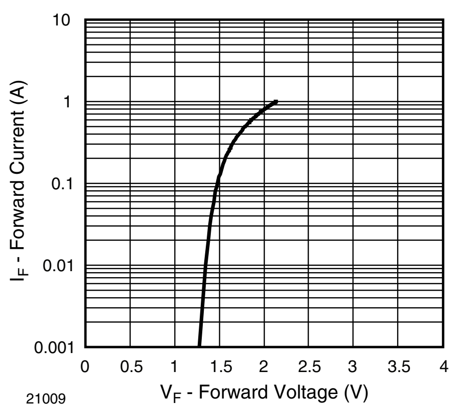


Fig. 4 - Forward Current vs. Forward Voltage

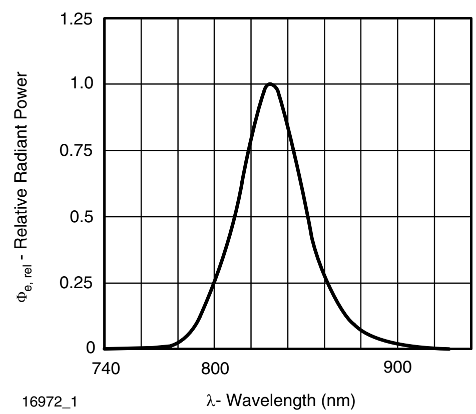


Fig. 7 - Relative Radiant Power vs. Wavelength

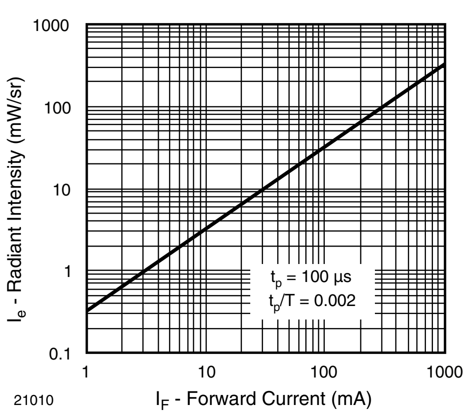


Fig. 5 - Radiant Intensity vs. Forward Current

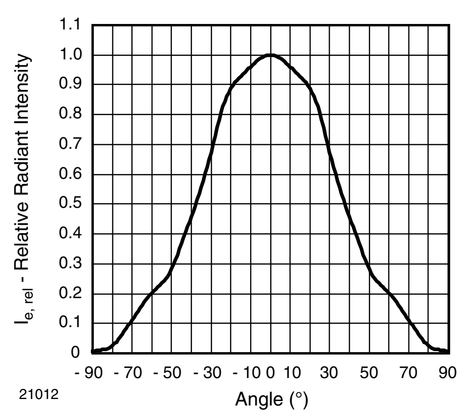
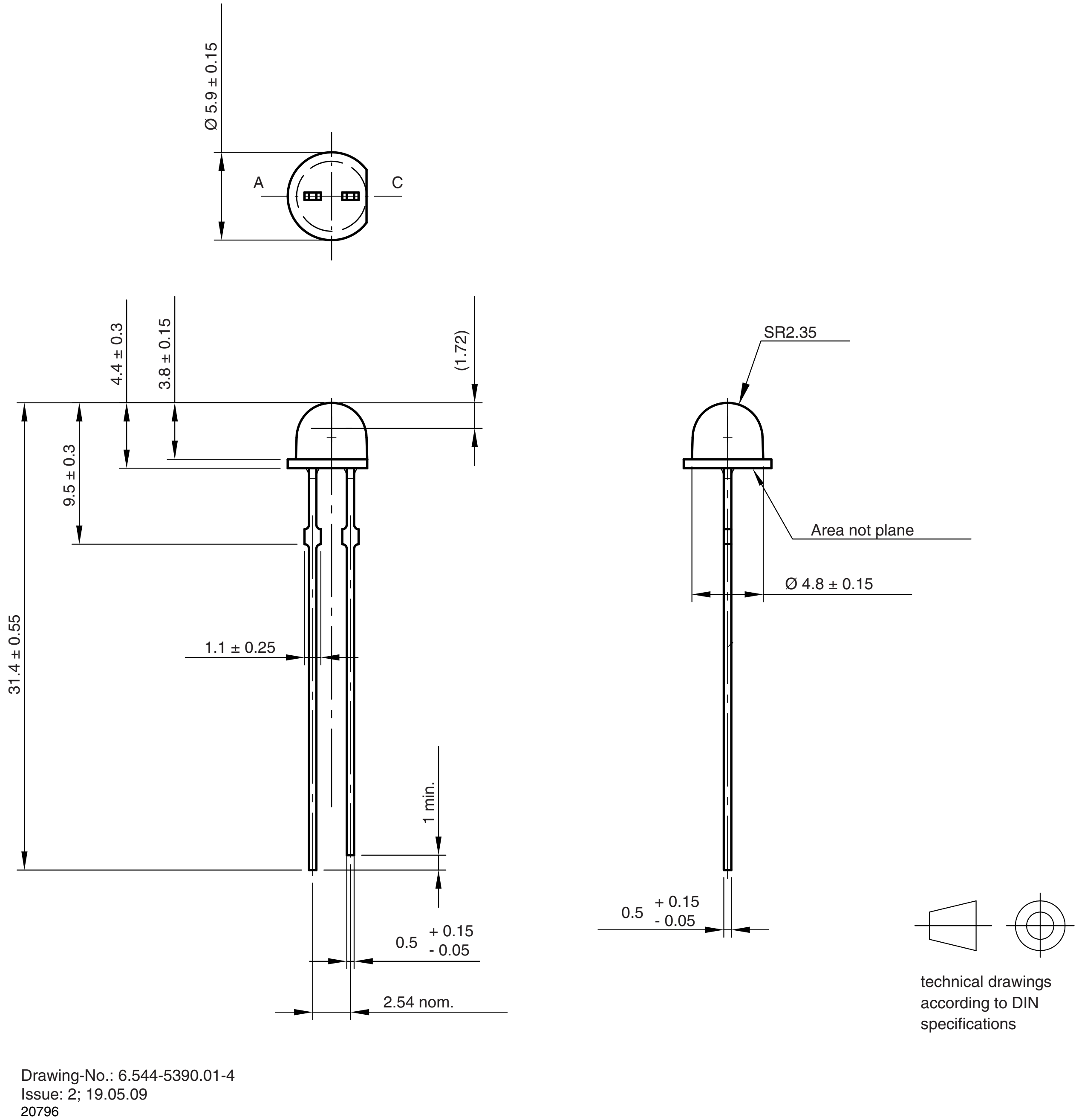


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



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